**Global Communication Semiconductors, LLC**
Corporate & Foundry
23155 Kashiwa Court, Torrance, CA 90505
Telephone: 310-530-7274 Fax: 310-517-8200
Website: www.gcsincorp.com

# Sr. GaN HEMT Device / Integration Engineer

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| Job Req. | #0703 |
| Department: | RF and Power Technology |
| Status: | Full-Time / Salaried |
| Shift: | Day |

## Job Description

- Lead GaN HEMT device/process development and yield improvement efforts, including 0.5um, 0.25um, and 0.15um GaN processes
- Responsible for device characterization and process qualifications
- Support trouble-shooting and yield improvement in related production processes
- Interact with customers and manufacturing staff
- Manage R&D projects

## Job Requirements

- Ph.D. or Master’s Degree in EE, Physics or Materials Science
- 5-10 years of industry experience in semiconductor wafer fab environment, including at least 4-6 years of direct hands-on experience in GaN HEMT technology